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September 2016



FDV045P20L

P-Channel PowerTrench® MOSFET

-20 V, -1.15 A, 108 mΩ

Features

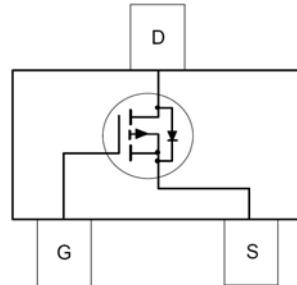
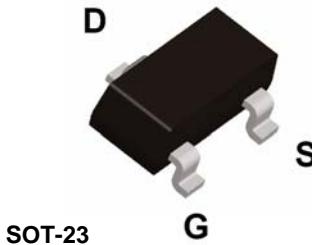
- Max $r_{DS(on)}$ = 108 mΩ at $V_{GS} = -4.5$ V, $I_D = -1.15$ A
- Max $r_{DS(on)}$ = 121 mΩ at $V_{GS} = -2.5$ V, $I_D = -0.7$ A
- Very low $r_{DS(on)}$ Mid Voltage P-channel Silicon Technology Optimised for Low Q_g
- This product is optimised for fast switching applications as well as load switch applications
- 100% UIL Tested
- RoHS Compliant

General Description

This P-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been optimized for the on-state resistance and yet maintain superior switching performance.

Applications

- Active Clamp Switch
- Load Switch



MOSFET Maximum Ratings $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	-20	V
V_{GS}	Gate to Source Voltage	± 8	V
I_D	-Continuous	(Note 1a)	A
	-Pulsed	(Note 4)	
E_{AS}	Single Pulse Avalanche Energy	(Note 3)	mJ
P_D	Power Dissipation	(Note 1a)	W
	Power Dissipation	(Note 1b)	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	80	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	180	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDV045P20L	FDV045P20L	SOT-23	7 "	8 mm	3000 units

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = -250 \mu\text{A}, V_{GS} = 0 \text{ V}$	-20			V
$\frac{\Delta \text{BV}_{\text{DSS}}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$, referenced to 25°C		-18		$\text{mV}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$		-1		μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 8 \text{ V}, V_{DS} = 0 \text{ V}$		± 100		nA

On Characteristics (Note 2)

$V_{GS(\text{th})}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = -250 \mu\text{A}$	-0.5	-0.9	-1.5	V
$\frac{\Delta V_{GS(\text{th})}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$, referenced to 25°C		3		$\text{mV}/^\circ\text{C}$
$r_{DS(\text{on})}$	Static Drain to Source On Resistance	$V_{GS} = -4.5 \text{ V}, I_D = -1.15 \text{ A}$		86	108	$\text{m}\Omega$
		$V_{GS} = -2.5 \text{ V}, I_D = -0.7 \text{ A}$		97	121	
		$V_{GS} = -1.8 \text{ V}, I_D = -0.5 \text{ A}$		121	160	
		$V_{GS} = -4.5 \text{ V}, I_D = -1.15 \text{ A}, T_J = 125^\circ\text{C}$		110	138	
g_{FS}	Forward Transconductance	$V_{DS} = -5 \text{ V}, I_D = -1.15 \text{ A}$		3		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		812	1220	pF
C_{oss}	Output Capacitance			119	167	pF
C_{rss}	Reverse Transfer Capacitance			108	151	pF
R_g	Gate Resistance			20		Ω

Switching Characteristics

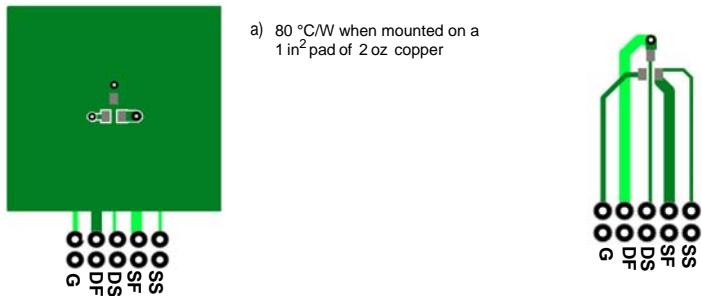
$t_{d(\text{on})}$	Turn-On Delay Time	$V_{DD} = -10 \text{ V}, I_D = -1.15 \text{ A}, V_{GS} = -4.5 \text{ V}, R_{\text{GEN}} = 6 \Omega$		8.4	17	ns	
t_r	Rise Time			6.5	13	ns	
$t_{d(\text{off})}$	Turn-Off Delay Time			76	122	ns	
t_f	Fall Time			26	42	ns	
Q_g	Total Gate Charge	$V_{GS} = 0 \text{ V to } -4.5 \text{ V}$		7.2	10	nC	
Q_g	Total Gate Charge		$V_{GS} = 0 \text{ V to } -2.5 \text{ V}$	$V_{DD} = -10 \text{ V}, I_D = -1.15 \text{ A}$	4.4	6.2	nC
Q_{gs}	Gate to Source Gate Charge				1.2		nC
Q_{gd}	Gate to Drain "Miller" Charge				1.8		nC

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = -1.15 \text{ A}$ (Note 2)		-0.8	-1.2	V
t_{rr}	Reverse Recovery Time	$I_F = -1.15 \text{ A}, dI/dt = 100 \text{ A}/\mu\text{s}$		11	20	ns
Q_{rr}	Reverse Recovery Charge				2	10

Notes:

- R_{QJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{QJC} is guaranteed by design while R_{QCA} is determined by the user's board design.



- Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.
- Starting $T_J = 25^\circ\text{C}$; P-ch: $L = 3 \text{ mH}, I_{AS} = -3 \text{ A}, V_{DD} = -20 \text{ V}, V_{GS} = -6.4 \text{ V}$.
- Pulsed I_d refer to Fig 10 SOA curve for more details.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted.

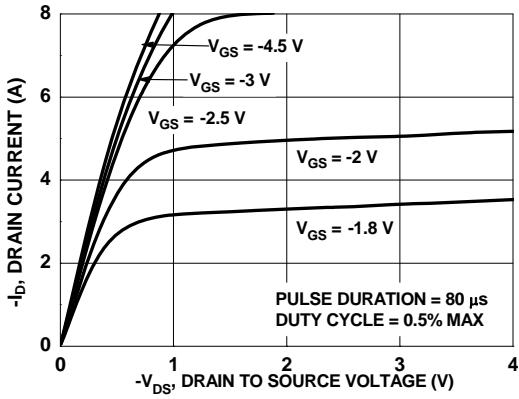


Figure 1. On Region Characteristics

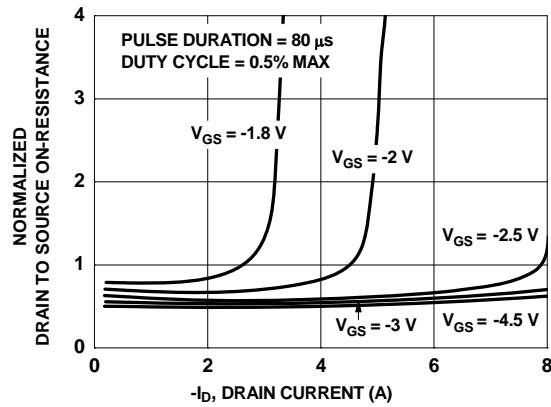


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

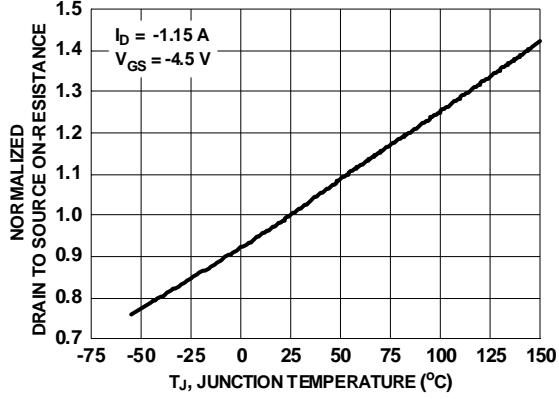


Figure 3. Normalized On Resistance vs. Junction Temperature

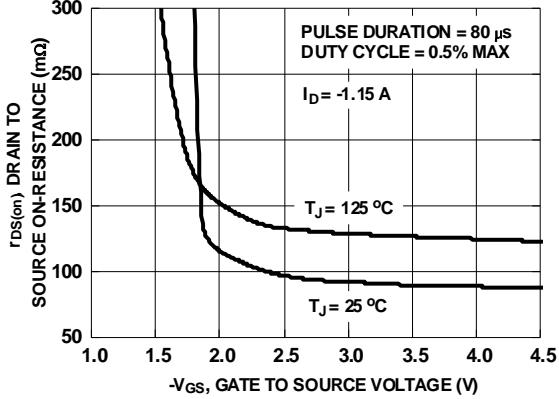


Figure 4. On-Resistance vs. Gate to Source Voltage

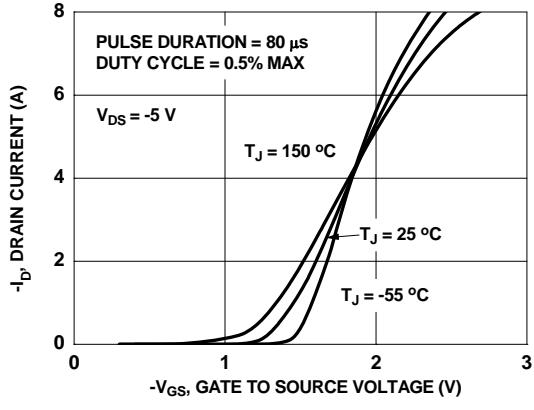


Figure 5. Transfer Characteristics

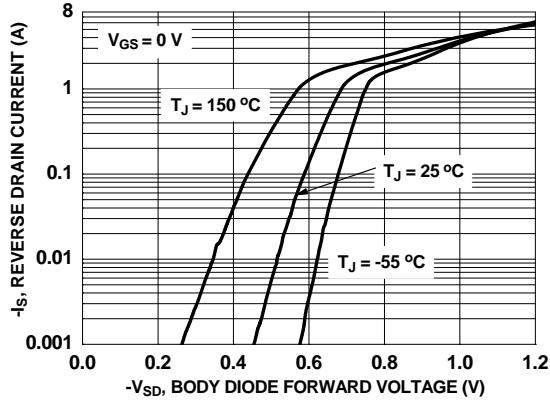


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted.

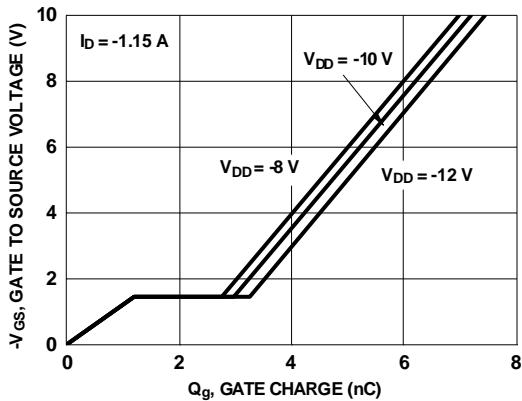


Figure 7. Gate Charge Characteristics

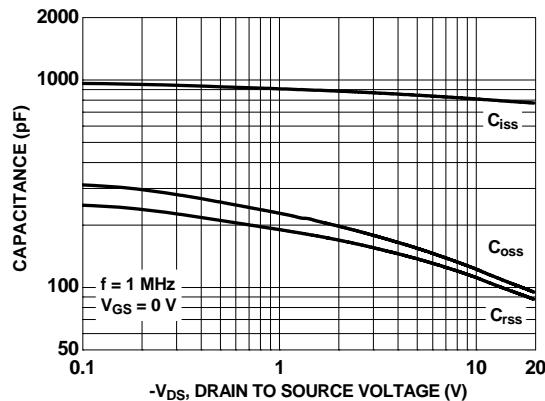


Figure 8. Capacitance vs. Drain to Source Voltage

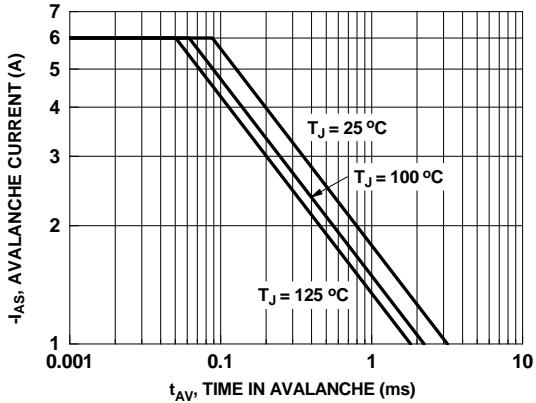


Figure 9. Unclamped Inductive Switching Capability

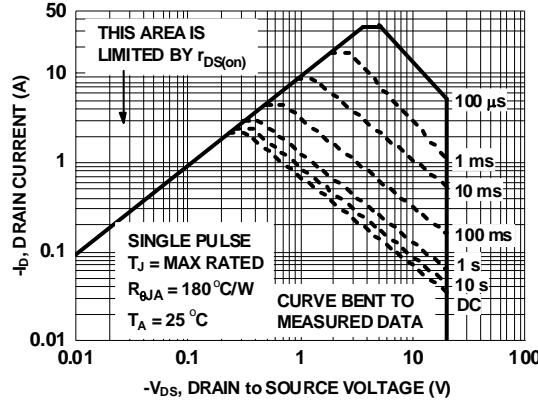


Figure 10. Forward Bias Safe Operating Area

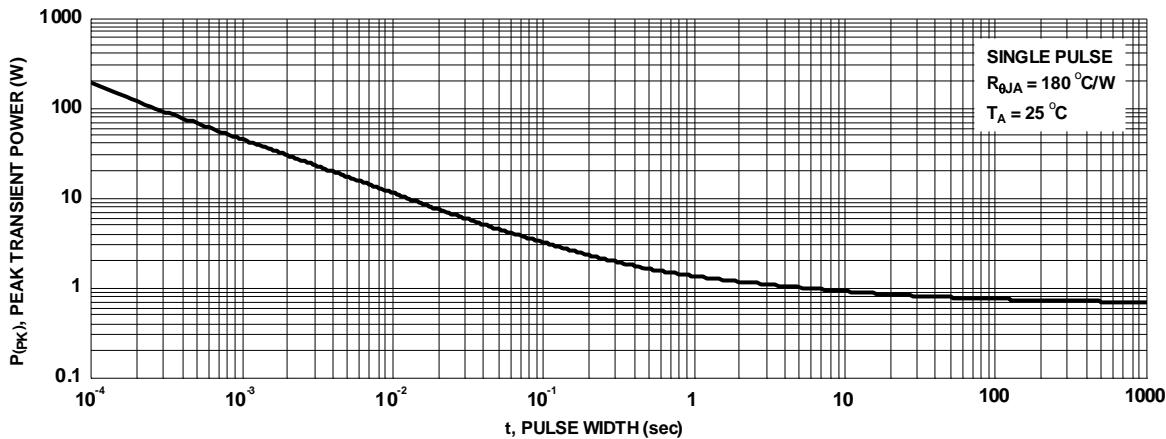


Figure 11. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted.

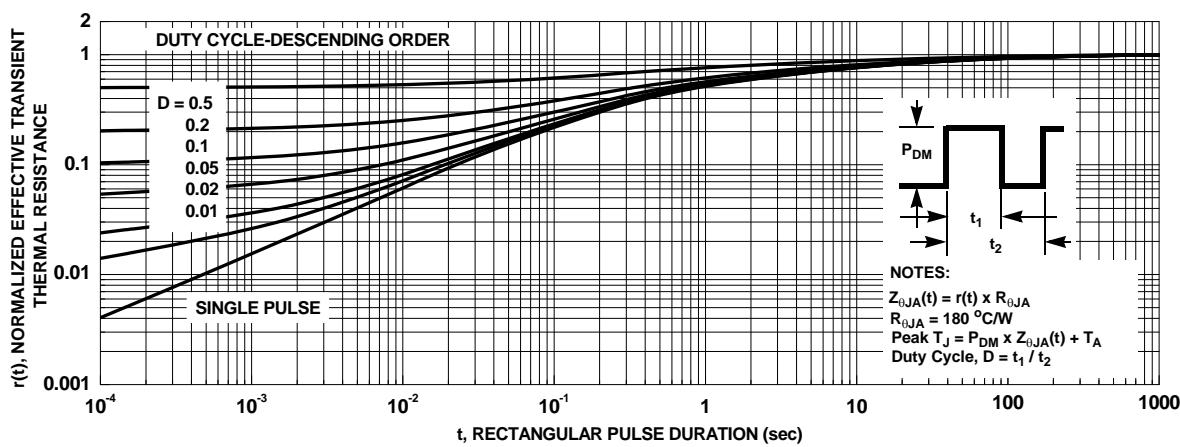


Figure 12. Junction-to-Ambient Transient Thermal Response Curve



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